

Electronic Supplementary Information

for

Suppression of Energy Dissipation and Enhancement of Breakdown Strength in Ferroelectric Polymer-Graphene Percolative Composites

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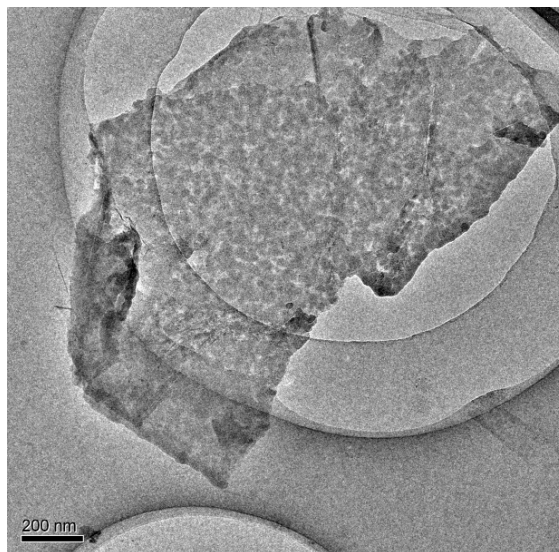


Fig.S1 TEM image of GO@SiO₂.

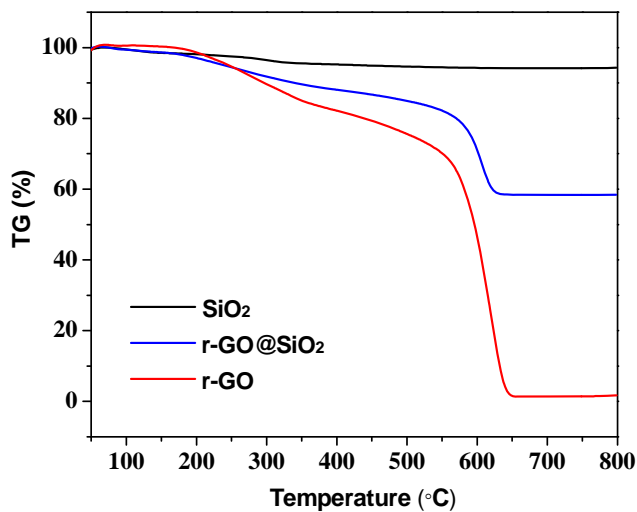


Fig.S2 TGA trace of SiO₂, r-GO@SiO₂ and r-GO.

Tab.S1 Atomic ratio of C, O, and Si elements in r-GO@SiO₂.

Element	C	O	Si
Atomic ratio (%)	48.0	36.7	15.3

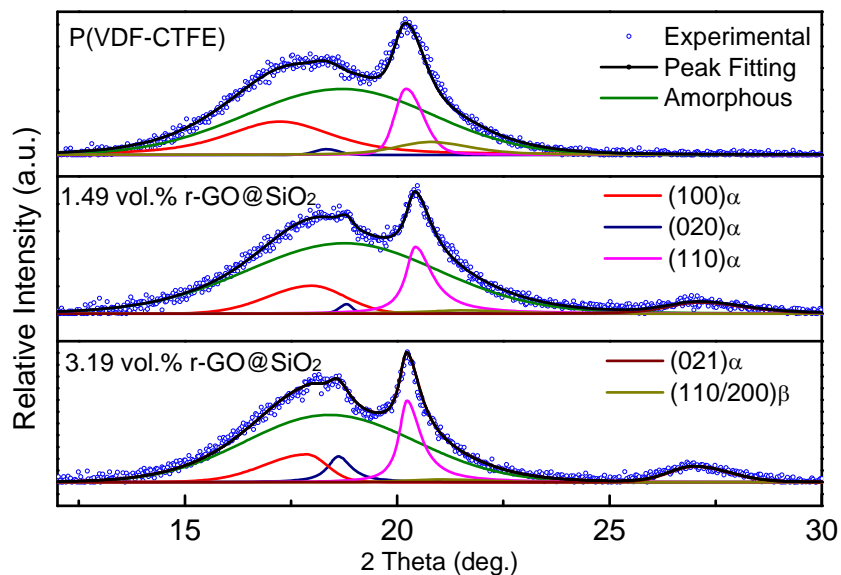


Fig.S3 XRD profiles of pure PVDF-CTFE, 1.49 vol.% r-GO@SiO₂ and 3.19 vol.% r-GO@SiO₂.

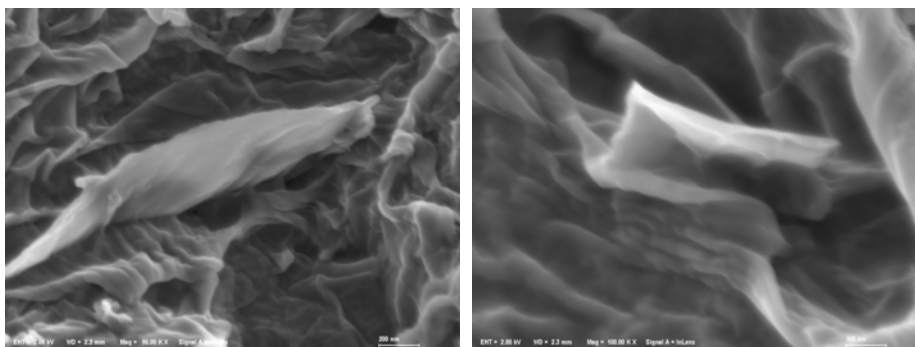


Fig.S4 SEM images of the fracture surface of the r-GO@SiO₂/P(VDF-CTFE) composite film. Scale bar: left: 200 nm, right: 100 nm.

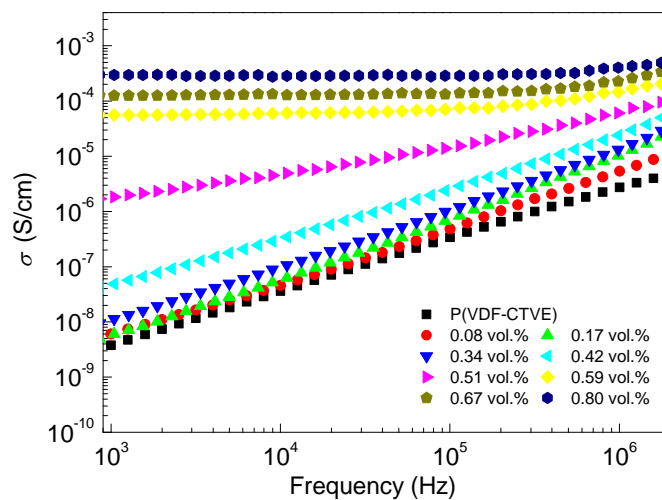


Fig.S5 Dependence of electrical conductivity of r-GO/P(VDF-CTFE) films on frequency.

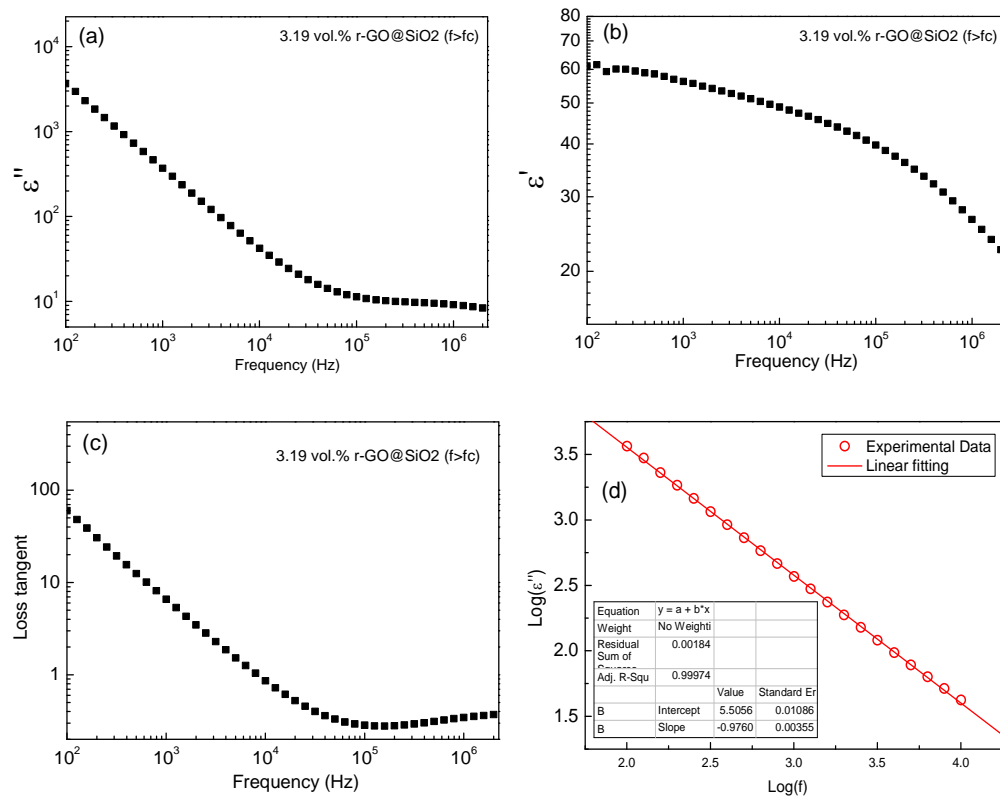


Fig.S6 Dependence of (a) imaginary part, (b) real part of dielectric permittivity and (c) loss tangent of r-GO/P(VDF-CTFE) on frequency. (d) Linear fitting of imaginary part of dielectric permittivity as a function of frequency, showing a slope very close to -1.

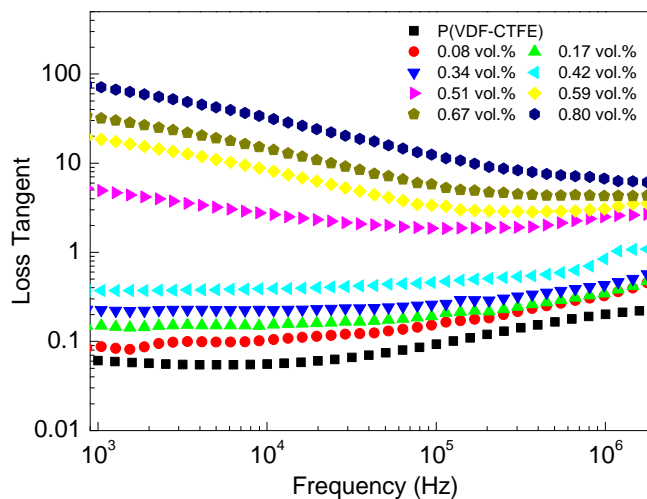


Fig.S7 Dependence of loss tangent of r-GO/P(VDF-CTFE) films on frequency.

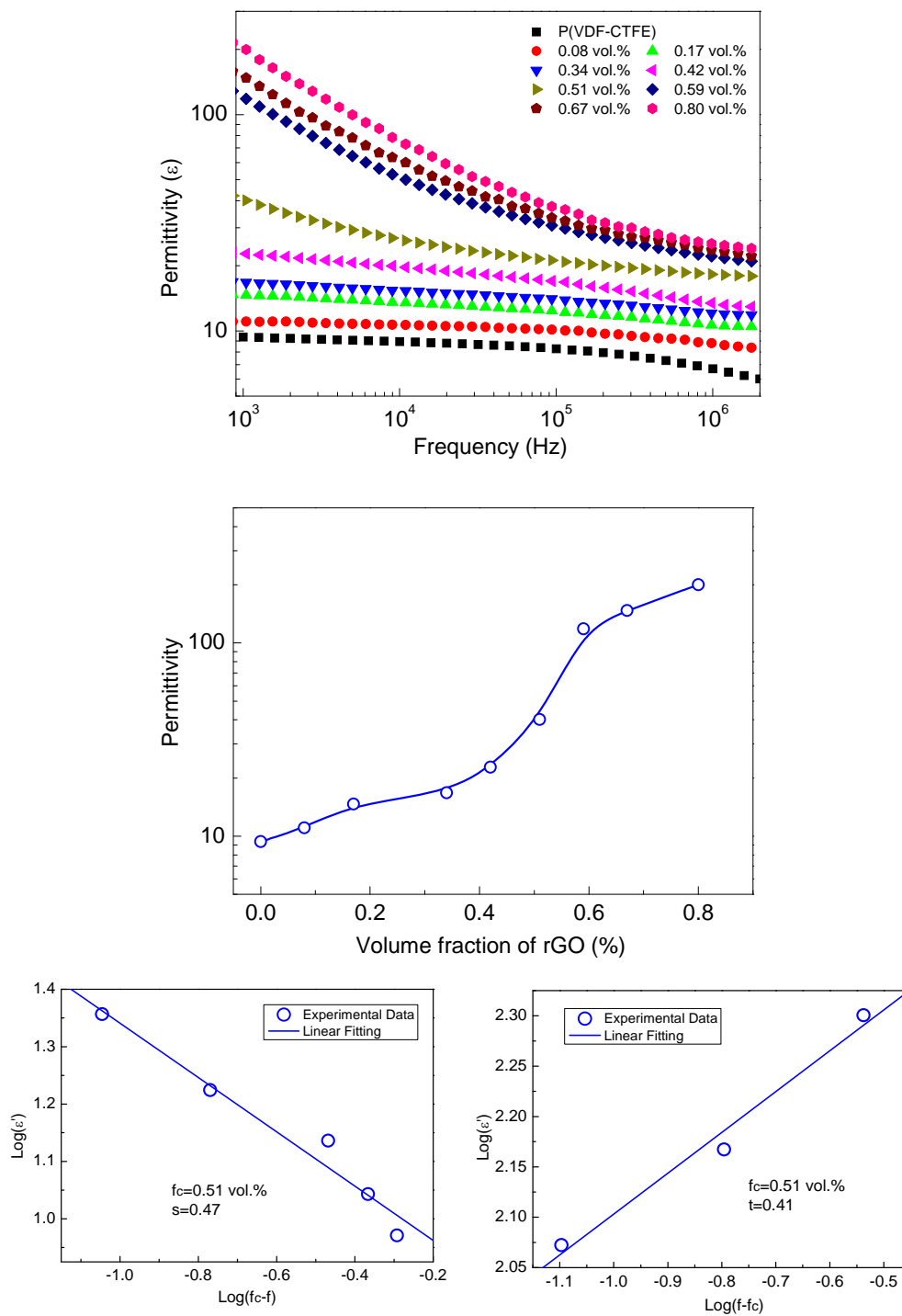


Fig.S8 Dependence of permittivity of r-GO/P(VDF-CTFE) composites on (a) the frequency and (b) the r-GO content at 1 KHz.